

In The Claims:

Claim 1. (original) A method for fabricating a thin film transistor (TFT), comprising:

forming a gate on a substrate, the gate comprising a MoNb alloy;

forming an insulating layer over the substrate covering the gate;

forming a channel layer on the insulating layer above the gate; and

forming a source/drain on the channel layer.

Claim 2. (original) The method of claim 1, wherein an amount of niobium in the MoNb alloy is less than 10%.

Claim 3. (original) The method of claim 1, wherein the gate comprises a composite layer of MoNb/AlNd or MoNb/AlNd/MoNb.

Claim 4. (original) The method of claim 3, wherein an amount of niobium in the MoNb alloy is less than 10%.

Claim 5. (original) The method of claim 1, wherein the source/drain comprises a single MoNb layer or a composite layer of MoNb/AlNd or MoNb/AlNd/MoNb.

Claim 6. (original) The method of claim 5, wherein an amount of niobium in the MoNb alloy is less than 10%.

Claim 7. (original) A method for fabricating a thin film transistor (TFT), comprising:

forming a gate on a substrate;

forming an insulating layer over the substrate covering the gate;

forming a channel layer on the insulating layer above the gate; and

forming a source/drain on the channel layer, the source/drain comprising a MoNb alloy.

Claim 8. (original) The method of claim 7, wherein an amount of niobium in the MoNb alloy is less than 10%.

Claim 9. (original) The method of claim 7, wherein the source/drain comprises a composite layer of MoNb/AlNd or MoNb/AlNd/MoNb.

Claim 10. (original) The method of claim 9, wherein an amount of niobium in the MoNb alloy is less than 10%.

Claim 11. (original) A thin film transistor (TFT), comprising:

a gate on a substrate, the gate comprising a MoNb alloy;

an insulating layer over the substrate covering the gate;

a channel layer on the insulating layer above the gate; and

a source/drain on the channel layer.

Claim 12. (original) The TFT of claim 11, wherein an amount of niobium in the MoNb alloy is less than 10%.

Claim 13. (original) The TFT of claim 11, wherein the gate comprises a composite layer of MoNb/AlNd or MoNb/AlNd/MoNb.

Claim 14. (original) The TFT of claim 13, wherein an amount of niobium in the MoNb alloy is less than 10%.

Claim 15. (original) The TFT of claim 11, wherein the source/drain comprises a single MoNb layer or a composite layer of MoNb/AlNd or MoNb/AlNd/MoNb.

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Claim 16. (original) The TFT of claim 15, wherein an amount of niobium in the MoNb alloy is less than 10%.

Claim 17. (currently amended) A thin film transistor (TFT), comprising:

a gate on a substrate;

an insulating layer over the substrate covering the gate;

a channel layer on the insulating layer above the gate; and

a source/drain on the channel layer, the source/drain comprising ~~a MoNb alloy~~ a composite layer of MoNb/AlNd or MoNb/AlNd/MoNb.

Claim 18. (original) The method of claim 17, wherein an amount of niobium in the MoNb alloy is less than 10%.

Claims 19-20 (canceled)